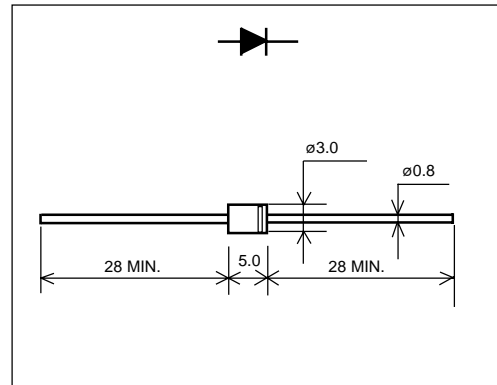


ERB43 (0.5A)

(200 to 800V / 0.5A)

FAST RECOVERY DIODE

■ Outline drawings, mm



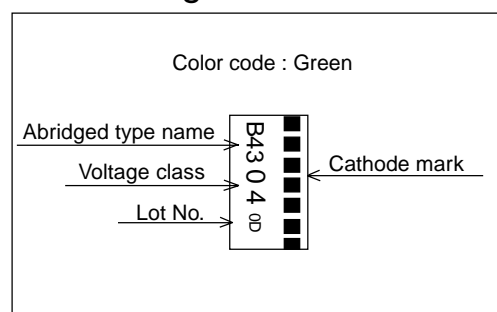
■ Features

- High voltage by mesa design
- High reliability

■ Applications

- High speed switching

■ Marking



■ Maximum ratings and characteristics

- Absolute maximum ratings

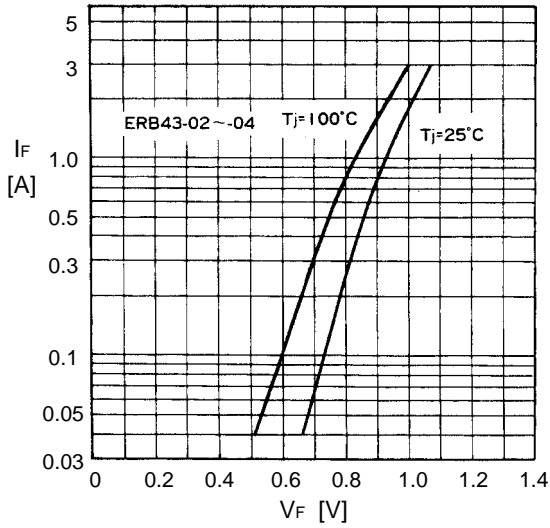
Item	Symbol	Conditions	Rating				Unit
			-02	-04	-06	-08	
Repetitive peak reverse voltage	V_{RRM}		200	400	600	800	V
Average forward current	$I_{F(AV)}$	Resistive load ($T_a=40^\circ\text{C}$)	0.5				A
Surge current	I_{FSM}	Sine wave 10ms	10				A
Operating junction temperature	T_j		-40 to +140				$^\circ\text{C}$
Storage temperature	T_{stg}		-40 to +140				$^\circ\text{C}$

- Electrical characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

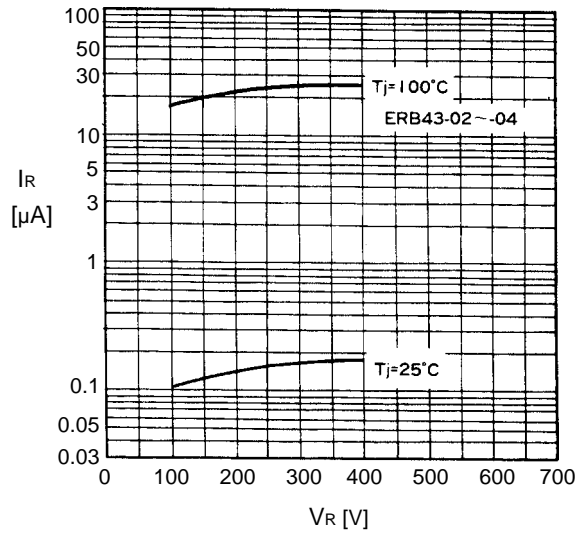
Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	$I_{FM}=0.5\text{A}$	1.2	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	10	μA
Reverse recovery time	t_{rr}	$I_F=0.1\text{A}, I_R=0.1\text{A}$	0.4	μs

■ Characteristics

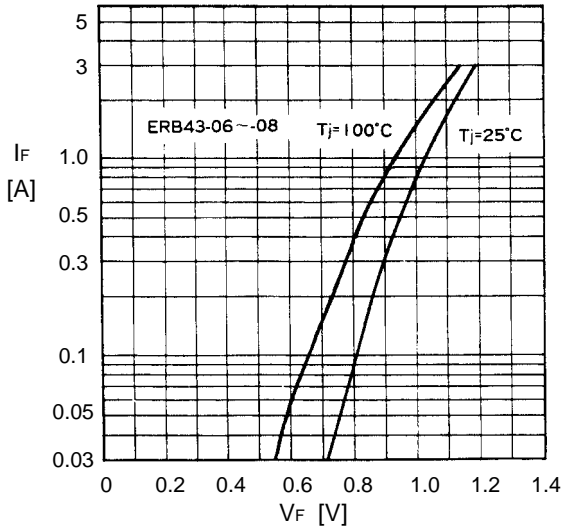
Forward characteristics



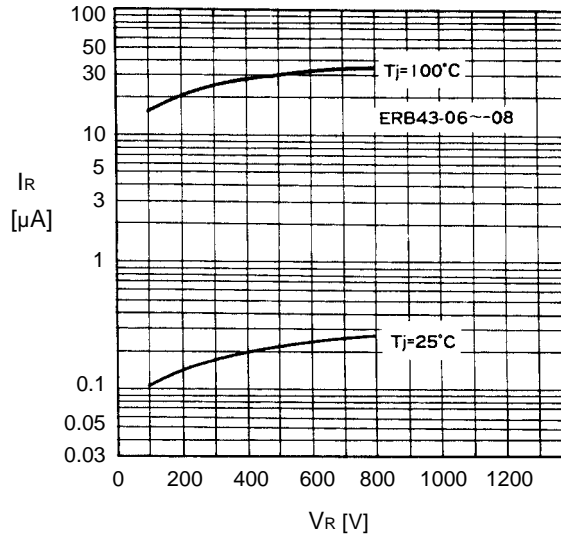
Reverse characteristics



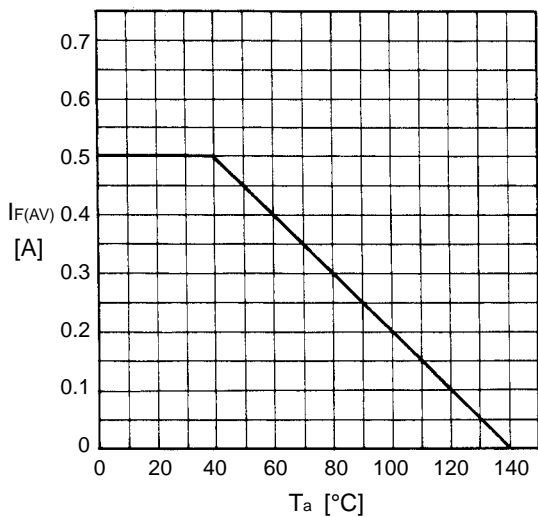
Forward characteristics



Reverse characteristics



Current derating ($I_{F(AV)}-T_a$)



Junction capacitance characteristics

